## **Darlington Amplifier Transistors**

**NPN Silicon** 

## MMBTA13L, SMMBTA13L, MMBTA14L, SMMBTA14L

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CES</sub>	30	Vdc
Collector - Base Voltage	$V_{CBO}$	30	Vdc
Emitter - Base Voltage	V <sub>EBO</sub>	10	Vdc
Collector Current – Continuous	Ic	300	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

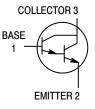


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SOT-23 (TO-236) **CASE 318** STYLE 6



#### MARKING DIAGRAM



1x = Device Code

x = M for MMBTA13LT1G, SMMBTA13LT1G x = N for MMBTA14LT1G, SMMBTA14LT1G, T3G

= Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MMBTA13LT1G, SMMBTA13LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA14LT1G, SMMBTA14LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBTA14LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

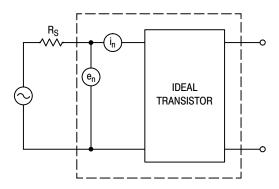
<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage ( $I_C = 100 \mu Adc, V_{BE} = 0$ )	V <sub>(BR)</sub> CES	30	-	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 30 Vdc, I <sub>E</sub> = 0)	Ісво	-	100	nAdc
Emitter Cutoff Current $(V_{EB} = 10 \text{ Vdc}, I_C = 0)$	I <sub>EBO</sub>	-	100	nAdc
ON CHARACTERISTICS (Note 3)	<u>.</u>			
DC Current Gain $ \begin{aligned} &(I_C=10 \text{ mAdc, V}_{CE}=5.0 \text{ Vdc})\\ &\text{MMBTA13, SMMBTA13}\\ &\text{MMBTA14, SMMBTA14}\\ &(I_C=100 \text{ mAdc, V}_{CE}=5.0 \text{ Vdc})\\ &\text{MMBTA13, SMMBTA13}\\ &\text{MMBTA14, SMMBTA13} \end{aligned} $	h <sub>FE</sub>	5000 10,000 10,000 20,000	- - -	_
Collector – Emitter Saturation Voltage (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0.1 mAdc)	V <sub>CE(sat)</sub>	-	1.5	Vdc
Base – Emitter On Voltage (I <sub>C</sub> = 100 mAdc, V <sub>CE</sub> = 5.0 Vdc)	V <sub>BE</sub>	-	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS	<u>.</u>			
Current – Gain – Bandwidth Product (Note 4) (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 100 MHz)	f <sub>T</sub>	125	-	MHz

<sup>3.</sup> Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.



**Figure 1. Transistor Noise Model** 

<sup>4.</sup>  $f_T = |h_{fe}| \bullet f_{test}$ .

#### **NOISE CHARACTERISTICS**

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$ 

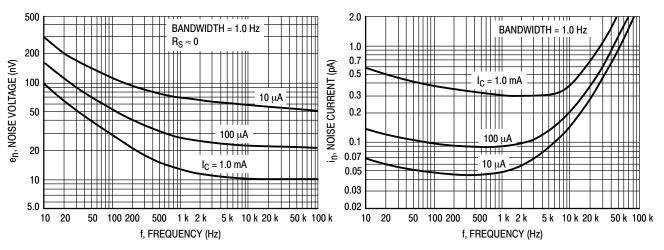


Figure 2. Noise Voltage

Figure 3. Noise Current

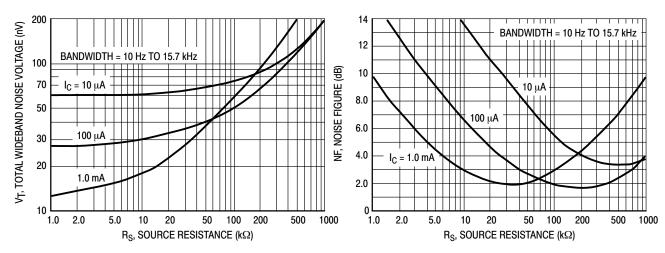


Figure 4. Total Wideband Noise Voltage

Figure 5. Wideband Noise Figure

#### **SMALL-SIGNAL CHARACTERISTICS**

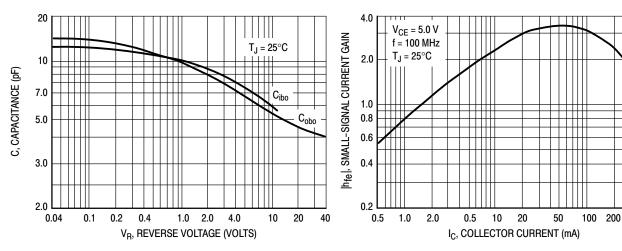


Figure 6. Capacitance

Figure 7. High Frequency Current Gain

500

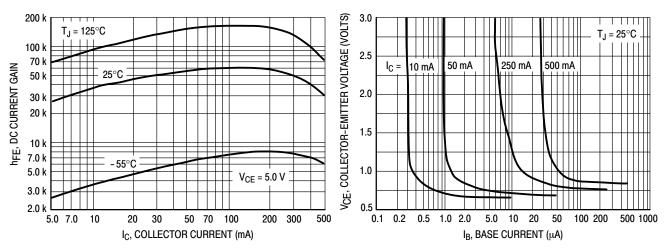


Figure 8. DC Current Gain

Figure 9. Collector Saturation Region

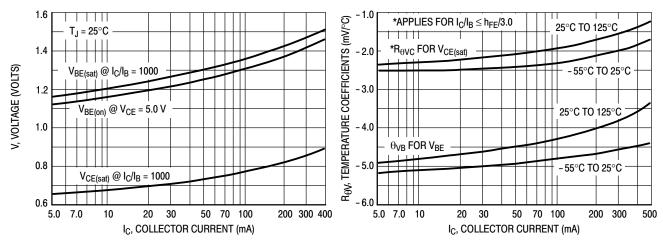


Figure 10. "On" Voltages

Figure 11. Temperature Coefficients

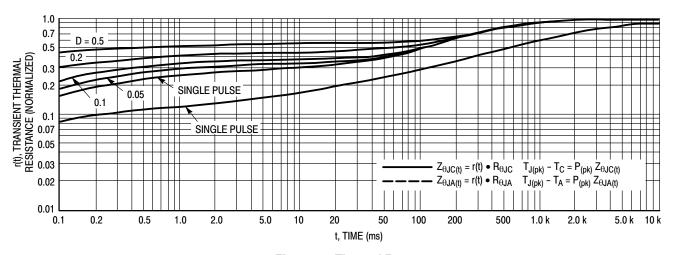


Figure 12. Thermal Response

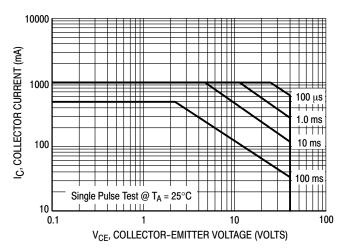
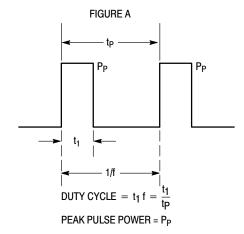


Figure 13. Active Region Safe Operating Area



**Design Note: Use of Transient Thermal Resistance Data** 

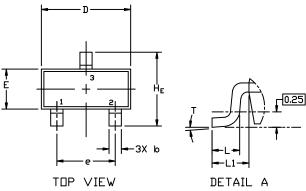




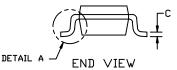
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**DATE 01 MAR 2023** 









#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

# GENERIC MARKING DIAGRAM\*

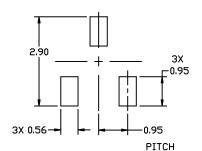


XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

#### **STYLES ON PAGE 2**

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## MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



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**DATE 01 MAR 2023** 

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: I PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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